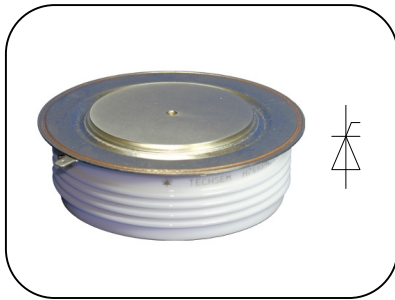


**Features:**

- Center amplifying gate
- Metal case with ceramic insulator
- Low on-state and switching losses

Typical Applications:

- AC controllers
- DC and AC motor control
- Controlled rectifiers

Part No. H125KPU-KT110dT

$I_{T(AV)}$	2800A
V_{DRM}, V_{RRM}	8000V
	8500V

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T_J (°C)	VALUE			UNIT
				Min	Type	Max	
$I_{T(AV)}$	Mean on-state current	180 half sine wave 50Hz Double side cooled	$T_C=55^\circ\text{C}$	90		2800	A
I_{DRM} I_{RRM}	Repetitive peak current	at V_{DRM} $t_p=10\text{ms}$ at V_{RRM} $t_p=10\text{ms}$	90			700	mA
I_{TSM}	Surge on-state current	10ms half sine wave	90			40	kA
I^2t	I^2t for fusing coordination	$V_R=0.6V_{RRM}$				8000	$10^3\text{A}^2\text{s}$
V_{TO}	Threshold voltage		90			0.92	V
r_T	On-state slope resistance					0.32	mΩ
V_{TM}	Peak on-state voltage	$I_{TM}=3000\text{A}$, $F=120\text{kN}$	25			1.95	V
dv/dt	Critical rate of rise of off-state voltage	$V_{DM}=0.67V_{DRM}$	90			2000	V/μs
di/dt	Critical rate of rise of on-state current	$V_{DM}=67\%V_{DRM}$, Gate pulse $t_r \leq 0.5\mu\text{s}$ $I_{GM}=1.5\text{A}$	90			100	A/μs
Q_{rr}	Recovery charge	$I_{TM}=2000\text{A}$, $t_p=4000\mu\text{s}$, $di/dt=-5\text{A}/\mu\text{s}$, $V_R=50\text{V}$	90		6500		μC
I_{GT}	Gate trigger current		25	40		300	mA
V_{GT}	Gate trigger voltage	$V_A=12\text{V}$, $I_A=1\text{A}$		0.8		3.0	V
I_H	Holding current			25		200	mA
V_{GD}	Non-trigger gate voltage	$V_{DM}=67\%V_{DRM}$	90			0.3	V
$R_{th(j-c)}$	Thermal resistance Junction to case	Double side cooled				0.004	C/W
$R_{th(c-h)}$	Thermal resistance case to heatsink	Clamping force 120kN				0.001	
F_m	Mounting force			110	120	140	kN
T_{vj}	Junction temperature			-40		90	°C
T_{stg}	Stored temperature			-40		140	°C
W_t	Weight				3420		g
Outline	KT110dT						

Outline:

